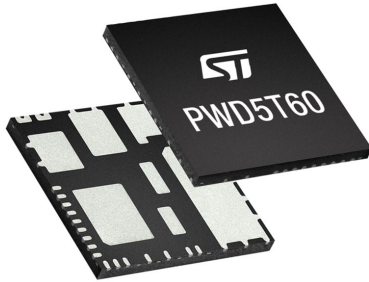


## Compact high-voltage three-phase power stage with integrated gate driver



VFQFPN12x12x0.95mm

### Features

- Power driver integrating gate driver and high-voltage power MOSFETs:
  - $R_{DS(on)} = 1.38 \Omega$
  - $BV_{DSS} = 500 \text{ V}$
- Wide input supply voltage range from 9 V to 20 V
- Integrated zero-drop bootstrap diodes
- Comparator for fast overcurrent protection with Smart ShutDown functionality
- Overtemperature protection
- 3.3 V, 5 V TTL/CMOS inputs with hysteresis
- Matched propagation delay for all channels
- UVLO function on low-side and high-side
- Interlocking and deadtime functions
- Dedicated enable pin
- Very compact and simplified layout

#### Product status link

[PWD5T60](#)

#### Product label



### Applications

- 3-phase inverters
- Fans and pumps
- Home and industrial appliances
- Refrigerator compressors

### Description

The PWD5T60 is a three-phase high-density power driver integrating gate driver and six N-channel power MOSFETs. The PWD5T60 is the optimal solution for motor drive applications such as fans, pumps and small appliances.

The integrated power MOSFETs have  $R_{DS(on)}$  of  $1.38 \Omega$  and 500 V blocking voltage. The high integration of the device allows to efficiently drive loads with reduced footprint, making PWD5T60 the optimal solution for space constrained applications.

The device has dedicated input pins for each output and a shutdown pin. The logic inputs are CMOS/TTL compatible down to 3.3 V for easy interfacing with control devices. Matched delays between low-side and high-side sections guarantee no cycle distortion and allow high-frequency operation.

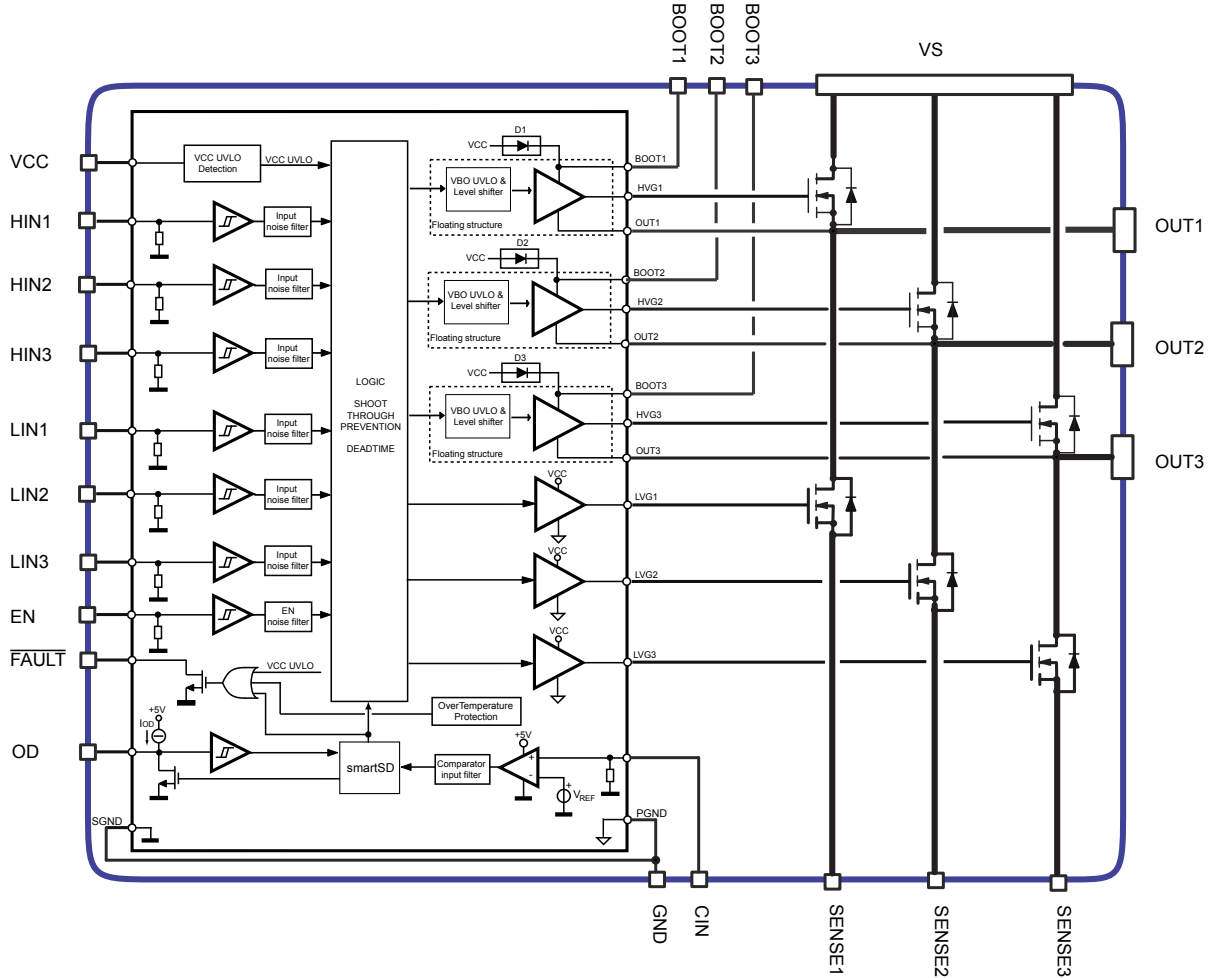
Robustness is a distinctive factor of PWD5T60. Prevention from cross conduction is ensured by interlocking and deadtime functions and a comparator featuring advanced smart ShutDown function ensures fast and effective protection against overload and overcurrent.

The dedicated UVLO protections on both low-side and high-side prevent the power switches from operating in low efficiency or dangerous conditions, enabling optimal and fail-safe operation.

The zero-drop integrated bootstrap diodes as well as all of the embedded features enable the design of compact and simple PCB layout, and reduce the overall bill of material and application cost. The device is available in a compact VFQFPN 12x12x0.95 mm.

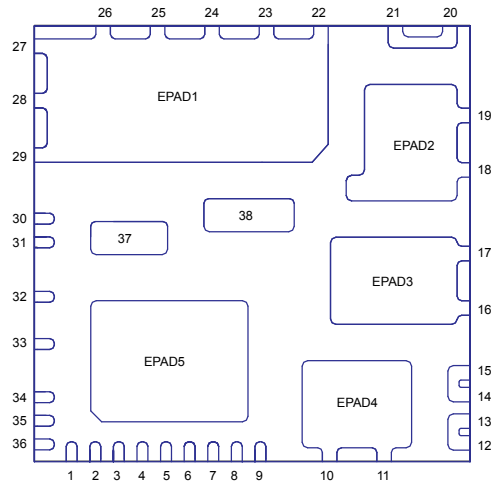
# 1 Block diagram

Figure 1. PWD5T60 block diagram



## 2 Pin description and connection diagram

**Figure 2. PWD5T60 pin connection**



**Table 1. Pin description**

Pin #	Pin Name	Type	Function
1	HIN3	Logic input	High-side driver logic input 3
2	LIN1	Logic input	Low-side driver logic input 1
3	LIN2	Logic input	Low-side driver logic input 2
4	LIN3	Logic input	Low-side driver logic input 3
5	FAULT	Open-drain output	Fault output
6	CIN	Analog input	Comparator positive input
7	EN	Logic input	Enable input, active high
8	OD	Open-drain output	SmartSD timing open-drain output, unlatch and restart input
9, EPAD5	GND	Power supply	Ground for gate driver IC and low-side gate drive return
10, 11, 30 <sup>(1)</sup> , 37, EPAD4	OUT1	Power	Half-bridge 1 output
12, 13	SENSE1	Power	Half-bridge 1 sense (low-side MOSFET source)
14, 15	SENSE2	Power	Half-bridge 2 sense (low-side MOSFET source)
16, 17, 38, EPAD3	OUT2	Power	Half-bridge 2 output
18, 19, EPAD2	OUT3	Power	Half-bridge 3 output
20, 21	SENSE3	Power	Half-bridge 3 sense (low-side MOSFET source)
22-29, EPAD1	Supply	Power supply	High voltage supply (high-side MOSFET drain)
31	BOOT1	Power supply	Bootstrap supply voltage 1
32	BOOT2	Power supply	Bootstrap supply voltage 2
33	BOOT3	Power supply	Bootstrap supply voltage 3
34	VCC	Power supply	Driver low side and logic supply voltage
35	HIN1	Logic input	High-side driver logic input 1
36	HIN2	Logic input	High-side driver logic input 2

1. Internally connected. Use for bootstrap capacitor connection only.

## 3 Electrical data

### 3.1 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in Table 2 may cause permanent damage to the device. Exposure to maximum rating conditions for extended periods may affect device reliability. All voltages referred to ground (GND) unless otherwise specified.

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Test Condition	Min	Max	Unit
VCC	Power supply voltage		-0.3	21	V
VCC-SENSE <sub>x</sub>	VCC to SENSE pin voltage		-0.3	25	V
V <sub>BO<sub>x</sub></sub>	BOOT to OUT pin		-0.3	21	V
BV <sub>DSS</sub>	MOSFETs blocking Voltage	T <sub>J</sub> = 25°C		500	V
I <sub>D</sub>	Drain current (per MOSFET)	DC @T <sub>CB</sub> = 25 °C <sup>(1)</sup>		3.5	A
		DC @T <sub>CB</sub> = 100 °C <sup>(1) (2)</sup>		2	A
		Peak @T <sub>CB</sub> = 25 °C <sup>(1) (2) (3)</sup>		14	A
SR <sub>OUT</sub>	Full bridge outputs slew rate (10% - 90%)	<sup>(2)</sup>		40	V/ns
V <sub>OUT<sub>x</sub></sub>	Output voltage		V <sub>BOOT<sub>x</sub></sub> - 21	500	V
V <sub>BOOT<sub>x</sub></sub>	Bootstrap voltage		-0.3	520	V
V <sub>CIN</sub>	Comparator input voltage		-0.3	20	V
V <sub>i</sub>	Logic input voltage <sup>(4)</sup>		- 0.3	15	V
V <sub>OD</sub>	Open-drain voltage (OD, FAULT)		-0.3	21	V
V <sub>FAULT</sub>	FAULT pin voltage		- 0.3	21	V
V <sub>ISO</sub>	Isolation Voltage (1 min) <sup>(2)</sup>			2500	V <sub>RMS</sub>
T <sub>J</sub>	Junction temperature		-40	125	°C
T <sub>stg</sub>	Storage temperature		-50	150	°C
P <sub>TOT</sub>	Total power dissipation <sup>(5)</sup>	T <sub>amb</sub> = 25°C JEDEC board <sup>(6) (7)</sup>		5.2	W
ESD	Human Body Model			2 <sup>(8)</sup>	kV

1. T<sub>CB</sub> is the temperature of the case-bottom pad.

2. Not tested in production.

3. The value specified by the design factor, pulse duration limited by max. junction temperature and SOA.

4. EN, LIN<sub>x</sub> and HIN<sub>x</sub> pins.

5. Value calculated basing on thermal resistance, power uniformity distributed over the six power MOSFETs, still air.

6. The device mounted on a FR4 2s2p board as JESD51-5/7.

7. Actual applicative board max. dissipation could be higher or lower depending on the layout and cooling techniques.

8. Pins 12, 13, 14, 15, 20 and 21 have HBM ESD value ± 1.75 kV

### 3.2 Recommended operating conditions

All voltages referred to ground (GND) unless otherwise specified.

**Table 3. Recommended operating conditions**

Symbol	Parameter	Min	Max	Unit
VCC	Power supply voltage	9	20	V
V <sub>BO</sub> <sup>(1)</sup>	Floating supply voltage	8.5	20	V
V <sub>OUT</sub>	DC Output voltage	-10 <sup>(2)</sup>	400 <sup>(3)</sup>	V
V <sub>CIN</sub>	Comparator input voltage	0	15	V
V <sub>i</sub>	Logic input voltage	0	15	V
V <sub>OD</sub>	Open-drain voltage (OD, FAULT)	0	20	V
V <sub>FAULT</sub>	FAULT pin voltage	0	20	V
f <sub>SW</sub> <sup>(4)</sup>	Maximum switching frequency		30	kHz
PW <sup>(5)</sup>	Minimum input pulse width	300		ns

1.  $V_{BO} = V_{BOOT} - V_{OUT}$

2. LVG off. VCC = 9 V. Logic is operational if  $V_{BOOT} > 5$  V.

3. At high temperature ( $T \geq 85$  °C) and high humidity ( $RH \geq 85\%$ ), the continuous operation at high voltage might induce acceleration of aging.

4. Actual maximum  $f_{SW}$  depends on power dissipation.

5. Pulse width on LIN or HIN pins propagated to gate driver outputs.

### 3.3 Thermal data

**Table 4. Thermal data**

Symbol	Parameter	Value	Unit
R <sub>th(J-CT)</sub>	Thermal resistance junction-to-case top	7	°C/W
R <sub>th(J-CB)</sub>	Thermal resistance junction-to-case bottom	0.32	°C/W

## 4 Electrical characteristics

### 4.1 Driver

HIN is referred to channels HIN1, HIN2, HIN3; LIN is referred to channels LIN1, LIN2, LIN3.

**Table 5. Electrical characteristics**

VCC = 15 V; T<sub>J</sub> = +25 °C, unless otherwise specified

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
<b>Low-side section supply</b>						
VCC <sub>thON</sub>	VCC UVLO turn on threshold		8.7	9.2	9.7	V
VCC <sub>thOFF</sub>	VCC UVLO turn off threshold		8.2	8.7	9.2	V
VCC <sub>hys</sub>	VCC UVLO hysteresis		0.4	0.5	0.6	V
I <sub>QCCU</sub>	VCC under-voltage quiescent supply current	VCC = 7 V; EN = 5 V; CIN = SGND LVG & HVG: OFF		430	744	μA
I <sub>QCC</sub>	VCC quiescent supply current	EN = 5 V; CIN = SGND LVG & HVG: OFF		1125	1650	μA
<b>High-side floating section supply <sup>(1)</sup></b>						
V <sub>BOthON</sub>	V <sub>BO</sub> UVLO turn on threshold		8.2	8.7	9.2	V
V <sub>BOthOFF</sub>	V <sub>BO</sub> UVLO turn off threshold		7.7	8.2	8.7	V
V <sub>BOhys</sub>	V <sub>BO</sub> UVLO hysteresis		0.4	0.5	0.6	V
I <sub>QBOU</sub>	V <sub>BO</sub> under-voltage quiescent supply current	VCC = V <sub>BO</sub> = 6.5 V; EN = 5 V; CIN = SGND LVG OFF; HVG = ON		25	62	μA
I <sub>QBO</sub>	V <sub>BO</sub> quiescent supply current	V <sub>BO</sub> = 15 V EN = 5 V; CIN = SGND LVG OFF; HVG = ON		84	150	μA
I <sub>LK</sub>	High voltage leakage current	BOOT = HVG = OUT = 520 V			15	μA
R <sub>Dboot</sub>	Bootstrap Diode on resistance			200		Ω
<b>Logic Inputs</b>						
V <sub>il</sub>	Low level logic threshold voltage		0.8		1.4	V
V <sub>ih</sub>	High level logic threshold voltage		1.8		2.3	V
V <sub>hyst</sub>	Logic input threshold hysteresis		0.8	0.9	1.2	V
V <sub>SSDh</sub>	SmartSD restart threshold		3.6	4.1	4.4	V
V <sub>SSDI</sub>	SmartSD unlatch threshold			0.56	0.75	V
I <sub>LINh</sub>	LIN logic "1" input bias current	V <sub>LINx</sub> = 15 V	120	150	200	μA
I <sub>LINl</sub>	LIN logic "0" input bias current	V <sub>LINx</sub> = 0 V			1	μA
I <sub>HINh</sub>	HIN logic "1" input bias current	V <sub>HINx</sub> = 15 V	120	150	200	μA
I <sub>HINl</sub>	HIN logic "0" input bias current+	V <sub>HINx</sub> = 0			1	μA
R <sub>PD_IN</sub>	Logic input pull-down resistor		75	100	125	kΩ
I <sub>ENh</sub>	EN logic "1" input bias current	V <sub>EN</sub> = 15 V	110	150	200	μA
I <sub>ENl</sub>	EN logic "0" input bias current	V <sub>EN</sub> = 0 V			1	μA
R <sub>PD_EN</sub>	EN pull-down resistor		75	100	125	kΩ

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
<b>Sense comparator <sup>(2)</sup> and <math>\overline{\text{FAULT}}</math></b>						
$V_{\text{REF}}$	Internal voltage reference		430	480	530	mV
$C_{\text{INHyst}}$	Comparator input hysteresis		40	70		mV
$C_{\text{IN\_PD}}$	Comparator input pull-down current	$V_{\text{CIN}} = 1 \text{ V}$	7	10	13	$\mu\text{A}$
$I_{\text{OD}}$	OD internal current source		2.5	5	7.5	$\mu\text{A}$
$R_{\text{ON\_OD}}$	OD On resistance	$I_{\text{OD}} = 16 \text{ mA}$	19	25	36	$\Omega$
$I_{\text{OL\_OD}}$	OD low level sink current	$V_{\text{OD}} = 400 \text{ mV}$	11	16	21	mA
$I_{\text{SAT\_OD}}$	OD saturation current	$V_{\text{OD}} = 5 \text{ V}$		108		mA
$V_{\text{FLOAT\_OD}}$	OD floating voltage level	OD connected only to an external capacitance	4.5	4.9	5.4	V
$R_{\text{ON\_F}}$	$\overline{\text{FAULT}}$ On resistance	$I_{\text{FAULT}} = 8 \text{ mA}$		50	100	$\Omega$
$I_{\text{OL\_F}}$	$\overline{\text{FAULT}}$ low level sink current	$V_{\text{FAULT}} = 400 \text{ mV}$	4	8	12	mA
$t_{\text{OD}}$	Comparator propagation delay	$R_{\text{pu}} = 100 \text{ k}\Omega$ to 5 V; Voltage step on CIN = 0 to 3.3 V; 50% CIN to 90% OD	350	4756	590	ns
$t_{\text{CIN-F}}$	Comparator triggering to $\overline{\text{FAULT}}$	Voltage step on CIN = 0 to 3.3 V; 50% CIN to 90% $\overline{\text{FAULT}}$	360	4758	590	ns
$t_{\text{CINoffMOS}}$	Comparator triggering to low-side MOSFET turn-off propagation delay	Voltage step on CIN = 0 to 3.3 V; OUT 500 $\Omega$ to 5 V, VS = 5 V 50% CIN to 10% OUT	730	840	950	ns
$t_{\text{FCIN}}$	Comparator input filter time		360	475	590	ns
SR	OD Slew rate	$C_{\text{L}} = 1 \text{ nF}$ ; $R_{\text{pu}} = 33 \text{ k}\Omega$ to 5 V; 90% to 10% OD	20	60	100	V/ $\mu\text{s}$
<b>Over temperature protection</b>						
$T_{\text{TSD}}$	Shut down temperature <sup>(3)</sup> <sup>(4)</sup>		120	135	150	$^{\circ}\text{C}$
$T_{\text{HYS}}$	Temperature hysteresis <sup>(3)</sup> <sup>(4)</sup>			20		$^{\circ}\text{C}$
<b>Dynamic characteristics</b>						
$t_{\text{FIN}}$	LIN, HIN input filter time		30	40	50	ns
$t_{\text{FEN}}$	EN input filter time		200	300	400	ns
DT	Deadtime	$C_{\text{L}} = 1 \text{ nF}$	200	300	400	ns
MDT	Matching deadtime <sup>(5)</sup>	$C_{\text{L}} = 1 \text{ nF}$		0	50	ns

- $V_{\text{BO}} = V_{\text{BOOT}} - V_{\text{OUT}}$
- Comparator is disabled when VCC is in UVLO condition
- Characterization data, not tested in production.
- The temperature sensor is located in the driver.
- $\text{MDT} = |DT_{\text{LH}} - DT_{\text{HL}}|$

## 4.2 Power MOSFETs

HIN is referred to channels HIN1, HIN2, HIN3; LIN is referred to channels LIN1, LIN2, LIN3.

**Table 6. Electrical characteristics**

VCC = 15 V; T<sub>J</sub> = +25 °C, unless otherwise specified.

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V <sub>(BR)DS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA <sup>(1)</sup>	600			V
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>DS</sub> = 500 V EN = SENSE = GND			1	μA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA <sup>(1)</sup>	3	4	5	V
R <sub>DS(on)</sub>	Static drain-source on-resistance	I <sub>D</sub> = 1.75 A; V <sub>GS</sub> = 10 V;	-	1.38	1.75	Ω
I <sub>AS</sub>	Avalanche current, repetitive or not repetitive	Pulse width limited by T <sub>J</sub> max. <sup>(1)</sup>			1	A
E <sub>AS</sub>	Single pulse avalanche energy	Starting T <sub>J</sub> = 25 °C, I <sub>D</sub> = I <sub>AS</sub> , V <sub>DD</sub> = 50 V <sup>(1)</sup>			132	mJ
V <sub>SD</sub>	Diode forward on voltage	EN = SENSE = GND I <sub>SD</sub> = 3.5 A;	-	-	1.6	V

1. Tested at wafer level before packaging.



## 5 Device characterization values

The PWD5T60 integrates six 500 V N-channel power MOSFETs in three phase full bridge configuration.

Table 7, Table 8. Inductive load switching characteristics and electrical characteristics curves contained in this section represent typical values based on characterization and simulation results and are not subject to the production test.

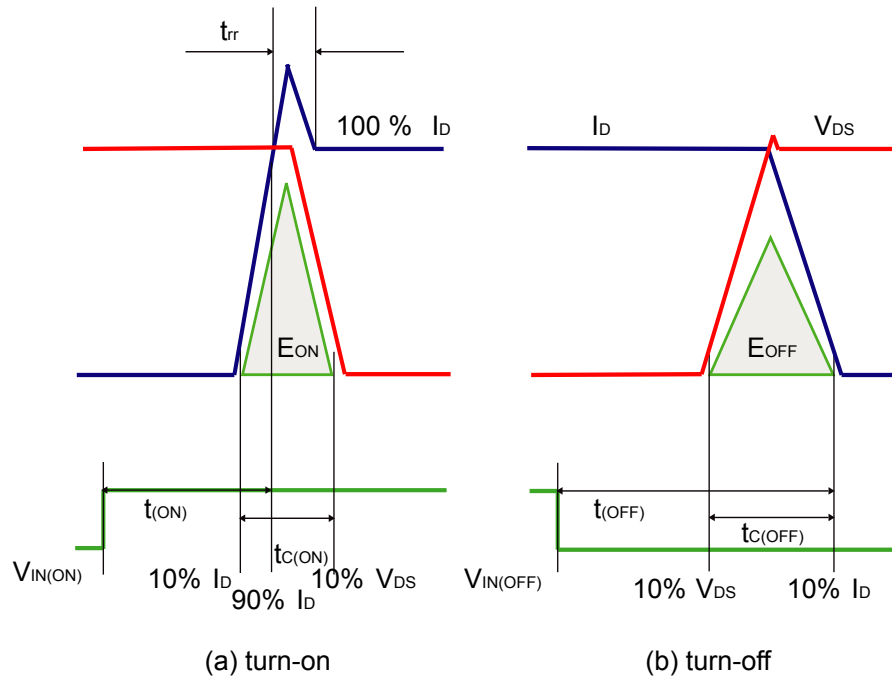
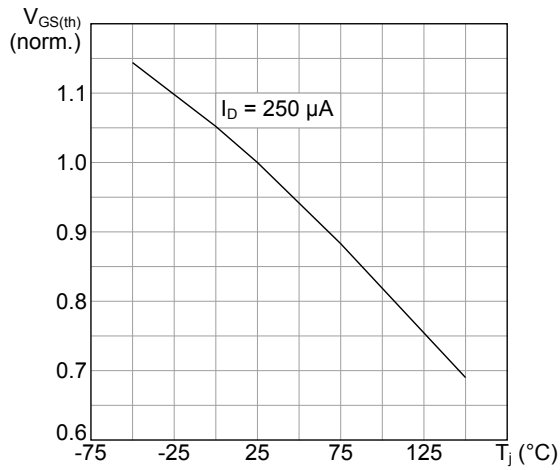
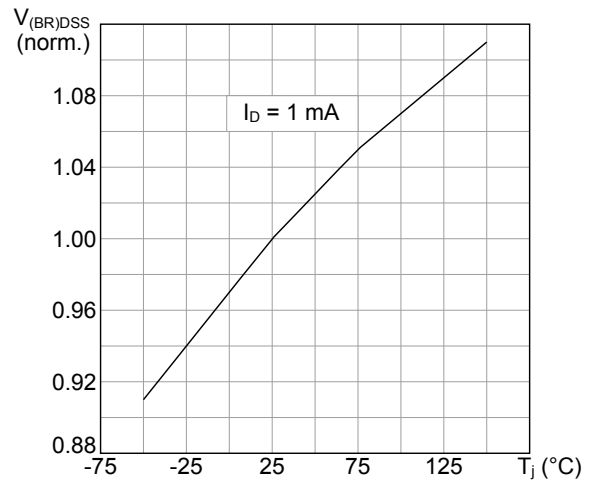
**Table 7. Power MOSFETs**

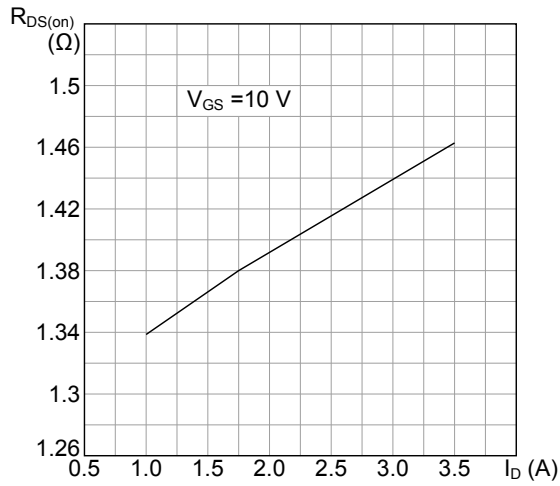
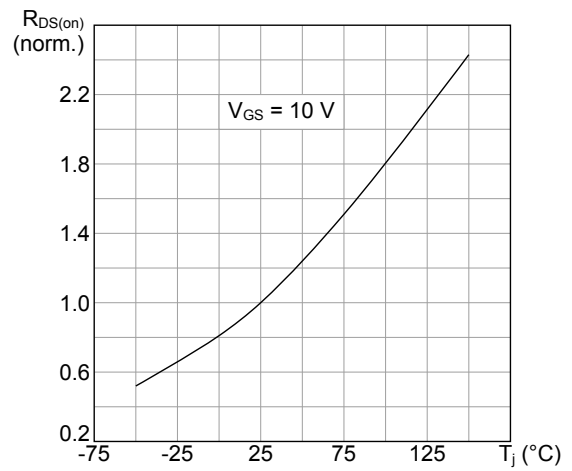
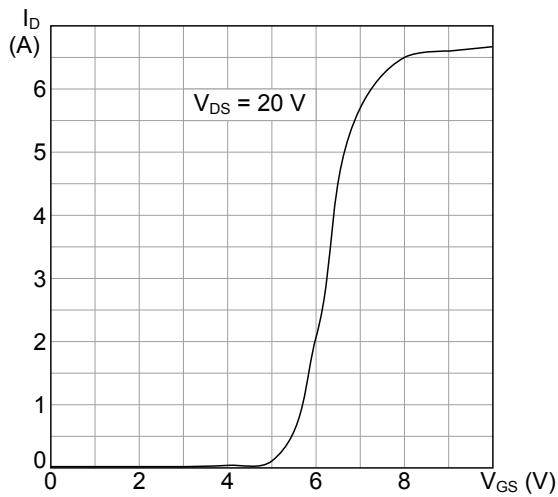
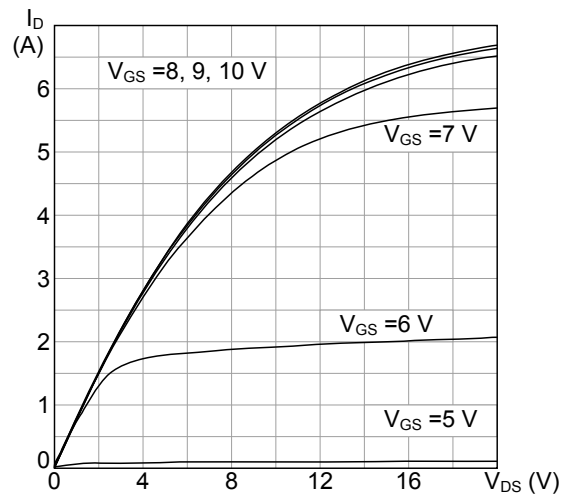
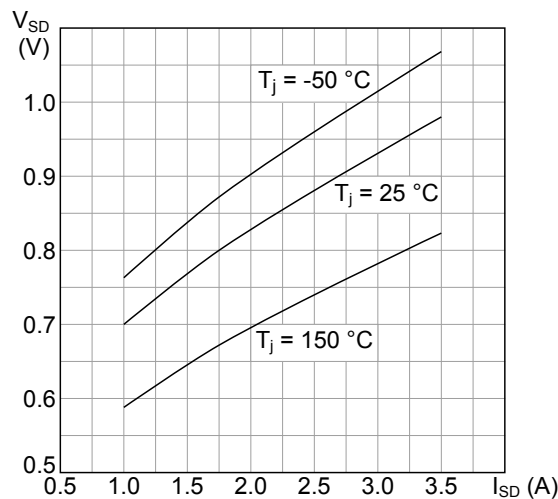
Symbol	Parameter	Test condition	Min	Typ	Max	Unit
<b>MOSFET Dynamic</b>						
$Q_g$	Total gate charge	$V_{GS} = 10\text{ V}$ , $T_J = 25\text{ °C}$ $V_{DS} = 480\text{ V}$ , $I_D = 3.5\text{ A}$	-	5.3	-	nC
<b>Source-Drain diode</b>						
$t_{rr}$	Diode reverse recovery time	$I_{SD} = 3.5\text{ A}$ , $T_J = 25\text{ °C}$	-	58	-	ns
$Q_{rr}$	Diode reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$ ,	-	109	-	$\mu\text{C}$
$I_{RRM}$	Diode reverse recovery current	$V_{DS} = 60\text{ V}$	-	4	-	A
$t_{rr}$	Diode reverse recovery time	$I_{SD} = 3.5\text{ A}$ , $T_J = 150\text{ °C}$	-	109	-	ns
$Q_{rr}$	Diode reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$ ,	-	309	-	$\mu\text{C}$
$I_{RRM}$	Diode reverse recovery current	$V_{DS} = 60\text{ V}$	-	5	-	A

**Table 8. Inductive load switching characteristics**

Symbol	Parameter	Test condition	Min	Typ	Max	Unit
$t_{(ON)}^{(1)}$	Turn-on time	$V_S = 300\text{ V}$ , $V_{CC} = V_{BO} = 15\text{ V}$ , $I_D = 1.75\text{ A}$ See Figure 3	-	390	-	ns
$t_{C(ON)}^{(2)}$	Crossover time (on)		-	150	-	ns
$t_{(OFF)}^{(1)}$	Turn-off time		-	165	-	ns
$t_{C(OFF)}^{(2)}$	Crossover time (off)		-	40	-	ns
$t_{SD}$	Shutdown to high/low-side propagation delay		-	HS: 75 LS: 85	-	ns
$E_{on}$	Turn-on switching losses		-	75	-	$\mu\text{J}$
$E_{off}$	Turn-off switching losses		-	8	-	$\mu\text{J}$

- $t_{(ON)}$  and  $t_{(OFF)}$  include the propagation delay time of the internal driver.
- $t_{C(ON)}$  and  $t_{C(OFF)}$  are the switching times of MOSFET itself under the internally given gate driving conditions.

**Figure 3. Switching time definition**

**Figure 4. Normalized gate threshold voltage vs temperature**

**Figure 5. Normalized drain-source breakdown voltage vs. temperature**


**Figure 6. Static drain-source on-resistance**

**Figure 7. Normalized on-resistance vs temperature**

**Figure 8. Transfer characteristics**

**Figure 9. Output characteristics**

**Figure 10. Static source-drain diode forward characteristics**


## 6 Functional description

### 6.1 Inputs and outputs

The device is controlled through the following logic inputs:

- EN: enable input, active high;
- LIN: low-side driver inputs, active high;
- HIN: high-side driver inputs, active high.

**Table 9. Inputs truth table (applicable when the device is not in UVLO or SmartSD protection)**

	Input pins			Output pins	
	EN	LIN	HIN	LVG	HVG
	L	X	X	OFF	OFF
	H	L	L	OFF	OFF
	H	H	L	<b>ON</b>	OFF
	H	L	H	OFF	<b>ON</b>
<i>Interlocking</i>	H	H	H	OFF	OFF

*Note:* X : Do not care.

The  $\overline{\text{FAULT}}$  and OD pins are open-drain outputs.

The  $\overline{\text{FAULT}}$  signal is set low in case VCC UVLO is detected, or in case the SmartShutDown comparator triggers an event. It is only used to signal a UVLO or SmartSD activation to external circuits, and its state does not affect the behavior of other functions or circuits inside the driver.

The OD behavior is explained in [Section 6.5](#).

### 6.2 Deadtime

The deadtime feature, in companion with the interlocking feature, guarantees that driver outputs of the same channel are not high simultaneously and at least a DT time passes between the turn-off of one driver's output and the turn-on of the companion output of the same channel. If a deadtime longer than the internal DT is applied to the LIN and HIN inputs by the external controller, the internal DT is ignored and the outputs follow the deadtime determined by the inputs.

### 6.3 VCC UVLO protection

Undervoltage protection is available on VCC and BOOT supply pins. In order to avoid intermittent operation, a hysteresis sets the turn-off threshold with respect to the turn-on threshold.

When VCC voltage goes below the  $V_{CCthOFF}$  threshold, all the outputs are switched off, both LVG and HVG. When VCC voltage reaches the  $V_{CCthON}$  threshold, the driver returns to normal operation and sets the LVG outputs according to actual input pin status; HVG is also set according to input pin status if the corresponding  $V_{BO}$  section is not in UVLO condition. The FAULT output is kept low when VCC is in UVLO condition. The following figures show some examples of typical operation conditions.

Figure 11. VCC power ON and UVLO, LVG timing

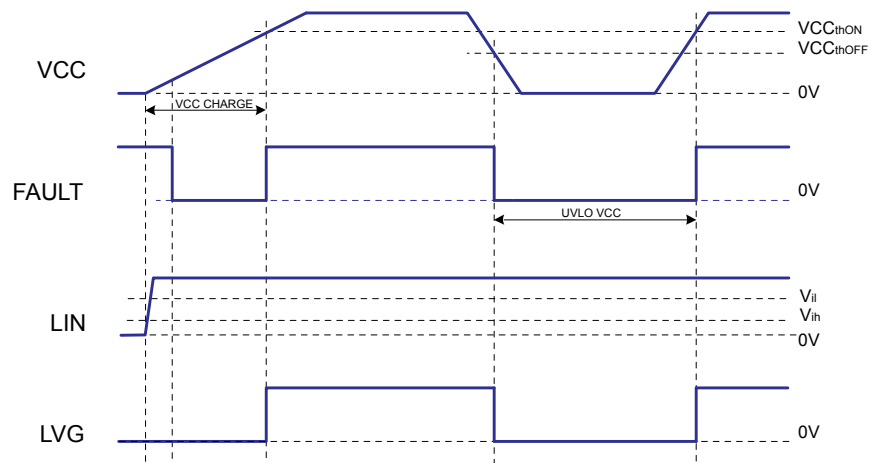
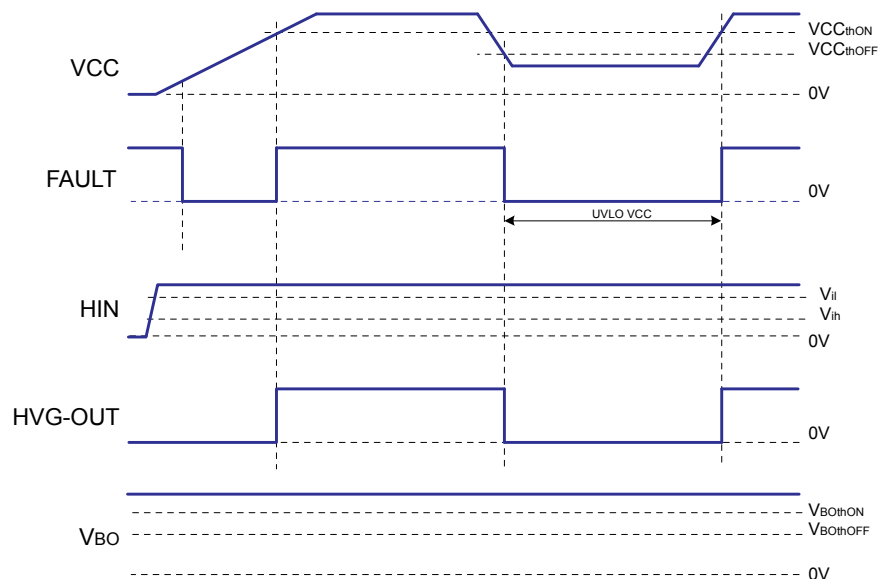


Figure 12. VCC power ON and UVLO, HVG timing

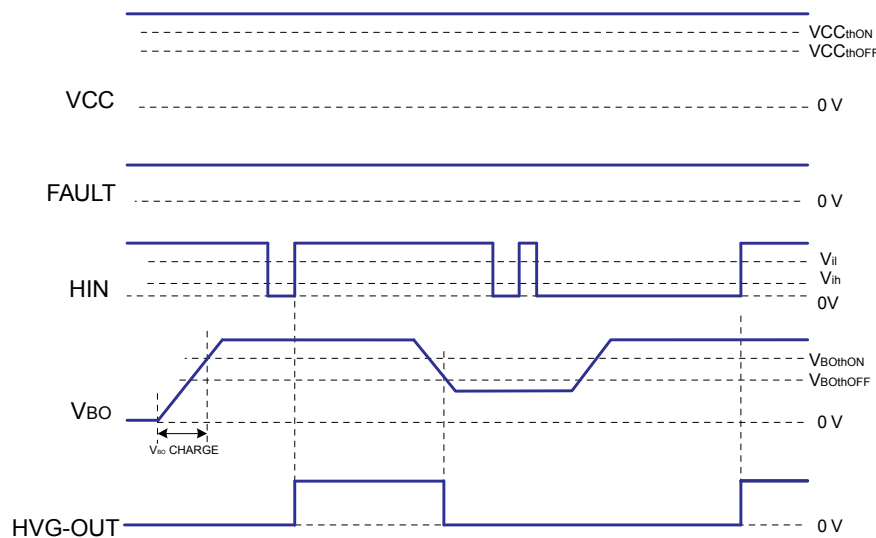


## 6.4 V<sub>BO</sub> UVLO protection

Dedicated undervoltage protection is available on each bootstrap section between BOOTx and OUTx supply pins. In order to avoid intermittent operation, a hysteresis sets the turn-off threshold with respect to the turn-on threshold.

When the V<sub>BO</sub> voltage goes below the V<sub>BOthOFF</sub> threshold, the HVG output of the corresponding bootstrap section is switched off. When the V<sub>BO</sub> voltage reaches the V<sub>BOthON</sub> threshold, the device returns to normal operation and the output remains off up to the next input pin transition that requests HVG to turn on.

Figure 13. V<sub>BO</sub> power-ON and UVLO timing



## 6.5 Comparator and Smart shutdown

The PWD5T60 integrates a comparator committed to the fault protection function, thanks to the SmartShutDown (SmartSD) circuit.

The SmartSD architecture allows immediate turn-off of the gate driver outputs in the case of overload or overcurrent condition, by minimizing the propagation delay between the fault detection event and the actual output switch-off. In fact, the time delay between the fault detection and the output turn-off is not dependent on the value of the external components connected to the OD pin, which are only used to set the duration of disable time after the fault.

This provides the possibility to increase the duration of the output disable time after the fault event up to very large values without increasing the delay time of the protection. The duration of the disable time is determined by the values of the external capacitor C<sub>OD</sub> and of the optional pull-up resistor connected to the OD pin.

The comparator has an internal voltage reference V<sub>REF</sub> connected to the inverting input, while the non-inverting input is available on the CIN pin. The comparator's CIN input can be connected to an external shunt resistor in order to implement a fast and simple overcurrent protection function. The output signal of the comparator is filtered from glitches shorter than t<sub>FCIN</sub> and then fed to the SmartSD logic.

If the impulse on the CIN pin is higher than V<sub>REF</sub> and wider than t<sub>FCIN</sub>, the SmartSD logic is triggered and immediately sets all of the driver outputs to low-level (OFF).

At the same time, FAULT is forced low to signal the event (for example to an MCU input) and OD starts to discharge the external C<sub>OD</sub> capacitor used to set the duration of the output disable time of the fault event.

The FAULT pin is released and driver outputs restart following the input pins as soon as the *output disable time* expires.

The overall disable time is composed of two phases:

- The OD *unlatch time* (t<sub>1</sub> in Figure 14), which is the time required to discharge the C<sub>OD</sub> capacitor down to the V<sub>SSDI</sub> threshold. The discharge starts as soon as the SSD comparator is triggered.

- The OD *Restart time* ( $t_2$  in Figure 14), which is the time required to recharge the  $C_{OD}$  capacitor up to the  $V_{SSDh}$  threshold. The recharge of  $C_{OD}$  starts when the OD internal MOSFET is turned-off, which happens when the fault condition has been removed ( $C_{IN} < V_{REF} - C_{INHyst}$ ) and the voltage on OD reaches the  $V_{SSDI}$  threshold. This time normally covers most of the overall output disable time.

If no external pull-up is connected to OD, the external  $C_{OD}$  capacitor is discharged with a time constant defined by  $C_{OD}$  and the internal MOSFET's characteristic (Equation 1), and the Restart time is determined by the internal current source  $I_{OD}$  and by  $C_{OD}$  (Equation 2).

**Equation 1**

$$t_1 \cong R_{ON\_OD} \cdot C_{OD} \cdot \ln\left(\frac{V_{OD}}{V_{SSDI}}\right) \quad (1)$$

**Equation 2**

$$t_2 \cong \frac{C_{OD} \cdot V_{SSDh}}{I_{OD}} \cdot \ln\left(\frac{V_{SSDI} - V_{OD}}{V_{SSDh} - V_{OD}}\right) \quad (2)$$

Where  $V_{OD} = V_{FLOAT\_OD}$

In case the OD pin is connected to VCC by an external pull-up resistor  $R_{OD\_ext}$ , the OD discharge time is determined by the external network  $R_{OD\_ext} C_{OD}$  and by the internal MOSFET's  $R_{ON\_OD}$  (Equation 3), while the Restart time is determined by current in  $R_{OD\_ext}$  (Equation 4).

**Equation 3**

$$t_1 \cong C_{OD} \cdot \left(R_{OD\_ext} // R_{ON\_OD}\right) \cdot \ln\left(\frac{V_{OD} - V_{on}}{V_{SSDI} - V_{on}}\right) \quad (3)$$

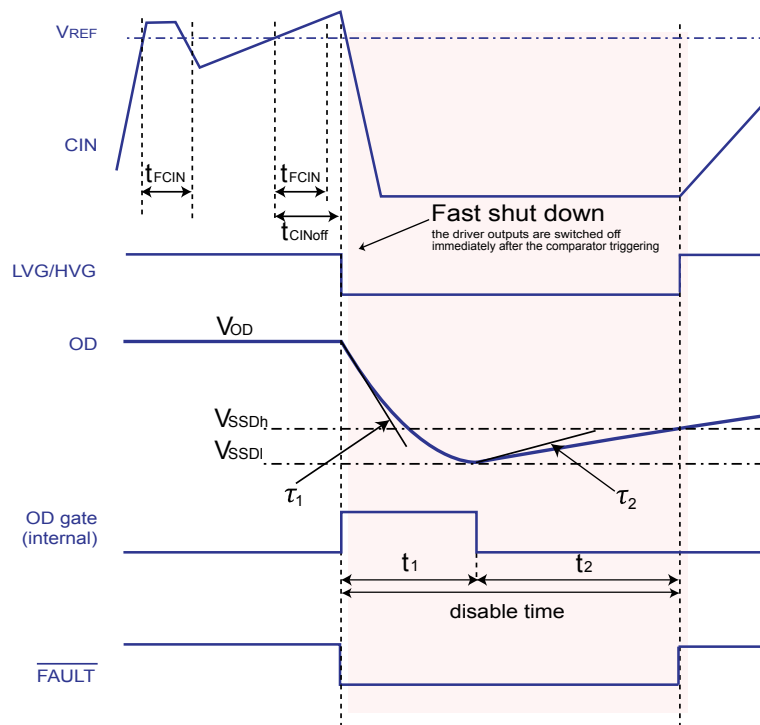
**Equation 4**

$$t_2 \cong C_{OD} \cdot R_{OD\_ext} \cdot \ln\left(\frac{V_{SSDI} - V_{OD}}{V_{SSDh} - V_{OD}}\right) \quad (4)$$

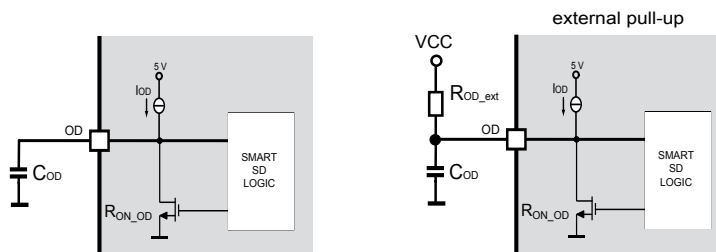
where:

$$V_{on} = \frac{R_{ON\_OD}}{R_{OD\_ext} + R_{ON\_OD}} \cdot VCC ; \quad V_{OD} = VCC$$

Figure 14. Smart shutdown timing waveforms



SMART SHUTDOWN CIRCUIT



## 6.6 Overtemperature protection

The device integrates an overtemperature protection, which turns and keeps all MOSFETs off when  $T_J$  exceeds  $T_{TSD}$ .

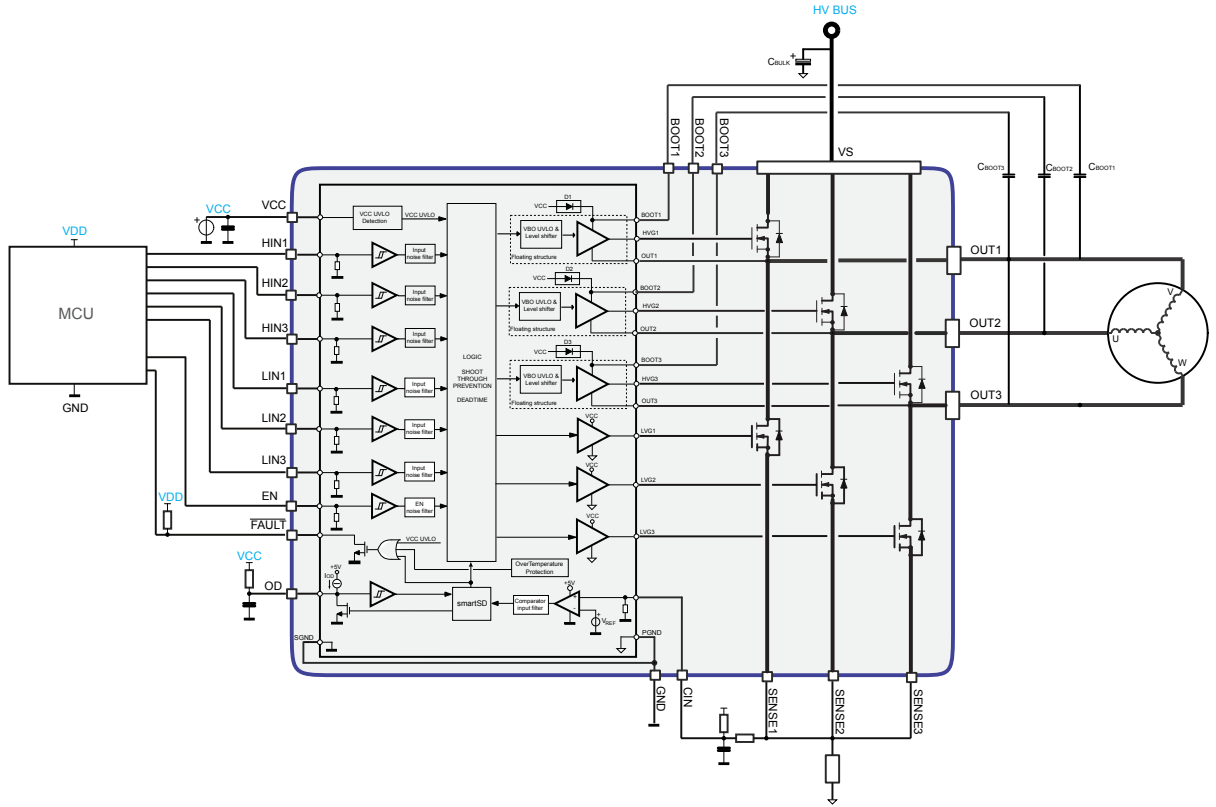
Overtemperature protection is signaled externally setting the  $\overline{FAULT}$  pin low.

Once  $T_J$  falls below  $(T_{TSD} - T_{HYS})$  the  $\overline{FAULT}$  pin is released and the MOSFETs are set according to the logic input values.



**7** Typ application

**Figure 15. Typical application 3-phase single-shunt**



## 8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

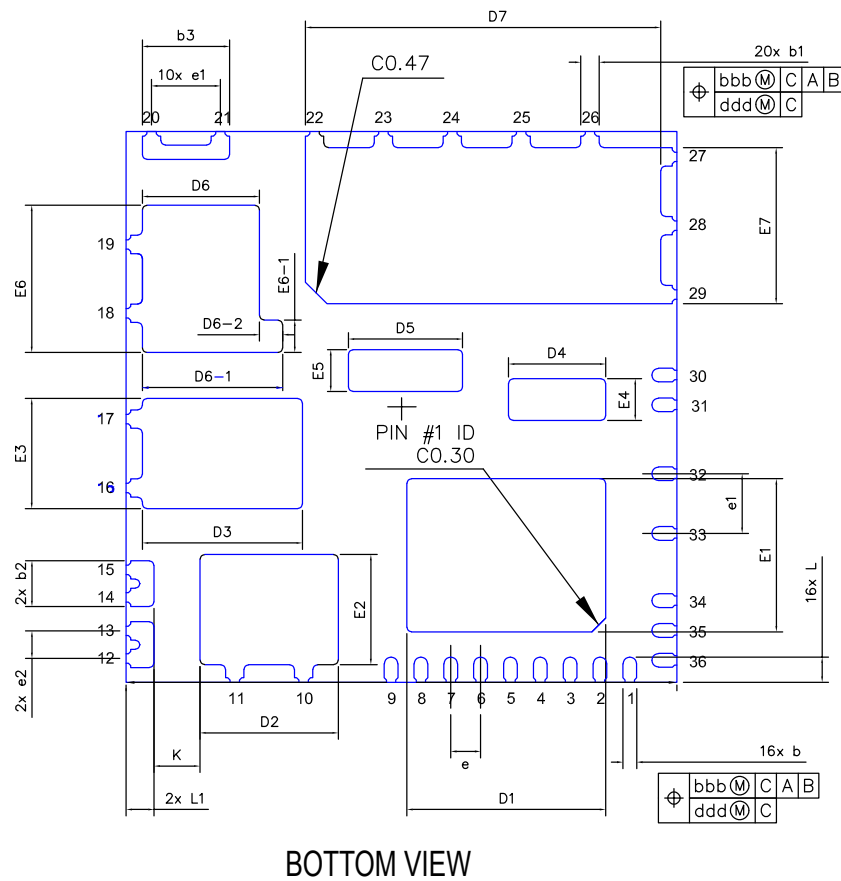
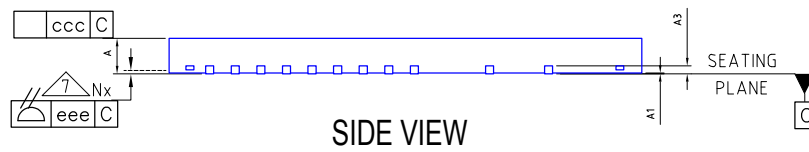
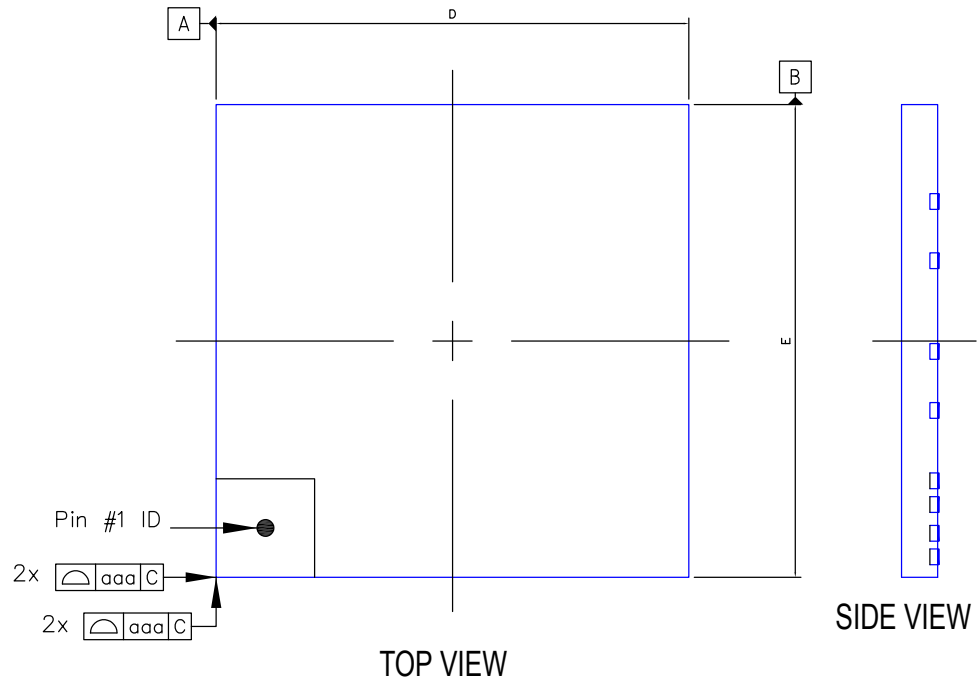
### 8.1 VFQFPN 12x12x0.95 mm, 36 leads, 0.65 mm pitch, package information

**Table 10. Package dimensions**

Symbol	Dimensions [mm]		
	Min.	Typ.	Max
A	0.80	0.90	1.00
A1	0.000	0.020	0.050
A3	0.203 REF		
b	0.25	0.30	0.35
b1	0.35	0.40	0.45
b2	0.95	1.00	1.05
b3	1.85	1.90	1.95
D	12.00 BSC		
E	12.00 BSC		
e	0.65 BSC		
e1	1.50 BSC		
e2	0.60 BSC		
e3	1.30 BSC		
D1	4.231	4.331	4.431
E1	3.236	3.336	3.436
D2	2.916	3.016	3.116
E2	2.300	2.400	2.500
D3	3.388	3.488	3.588
E3	2.300	2.400	2.500
D4	2.020	2.120	2.220
E4	0.812	0.912	1.012
D5	2.388	2.488	2.588
E5	0.812	0.912	1.012
D6	2.452	2.552	2.652
D6-1	2.956	3.056	3.156
D6-2	0.404	0.504	0.604
E6	3.108	3.208	3.308
E6-1	0.605	0.705	0.805
D7	7.640	7.740	7.840
E7	3.300	3.400	3.500
K	0.900	1.000	1.100
L	0.450	0.550	0.650

Symbol	Dimensions [mm]		
	Min.	Typ.	Max
L1	0.508	0.608	0.708
	TOLERANCE		
aaa		0.150	
bbb		0.100	
ccc		0.100	
ddd		0.050	
eee		0.080	

Figure 16. Package outline





## 9 Ordering information

**Table 11. Order code**

Order code	Package	Package marking	Packaging
PWD5T60	VFQFPN 12x12x0.95 mm, 36 leads, 0.65 mm pitch	PWD5T60	Tray
PWD5T60TR	VFQFPN 12x12x0.95 mm, 36 leads, 0.65 mm pitch	PWD5T60	Tape & reel

## Revision history

**Table 12. Document revision history**

Date	Version	Changes
15-Jan-2024	1	Initial release.

## Contents

<b>1</b>	<b>Block diagram</b> .....	<b>2</b>
<b>2</b>	<b>Pin description and connection diagram</b> .....	<b>3</b>
<b>3</b>	<b>Electrical data</b> .....	<b>4</b>
<b>3.1</b>	Absolute maximum ratings .....	4
<b>3.2</b>	Recommended operating conditions .....	5
<b>3.3</b>	Thermal data .....	5
<b>4</b>	<b>Electrical characteristics</b> .....	<b>6</b>
<b>4.1</b>	Driver .....	6
<b>4.2</b>	Power MOSFETs .....	8
<b>5</b>	<b>Device characterization values</b> .....	<b>9</b>
<b>6</b>	<b>Functional description</b> .....	<b>12</b>
<b>6.1</b>	Inputs and outputs .....	12
<b>6.2</b>	Dedtime .....	12
<b>6.3</b>	VCC UVLO protection .....	13
<b>6.4</b>	V <sub>BO</sub> UVLO protection .....	14
<b>6.5</b>	Comparator and Smart shutdown .....	14
<b>6.6</b>	Overtemperature protection .....	16
<b>7</b>	<b>Typ application</b> .....	<b>17</b>
<b>8</b>	<b>Package information</b> .....	<b>18</b>
<b>8.1</b>	VFQFPN 12x12x0.95 mm, 36 leads, 0.65 mm pitch, package information .....	18
<b>8.2</b>	Suggested footprint .....	21
<b>9</b>	<b>Ordering information</b> .....	<b>22</b>
	<b>Revision history</b> .....	<b>23</b>
	<b>List of tables</b> .....	<b>25</b>
	<b>List of figures</b> .....	<b>26</b>



## List of tables

<b>Table 1.</b>	Pin description . . . . .	3
<b>Table 2.</b>	Absolute maximum ratings . . . . .	4
<b>Table 3.</b>	Recommended operating conditions . . . . .	5
<b>Table 4.</b>	Thermal data . . . . .	5
<b>Table 5.</b>	Electrical characteristics . . . . .	6
<b>Table 6.</b>	Electrical characteristics . . . . .	8
<b>Table 7.</b>	Power MOSFETs . . . . .	9
<b>Table 8.</b>	Inductive load switching characteristics . . . . .	9
<b>Table 9.</b>	Inputs truth table (applicable when the device is not in UVLO or SmartSD protection) . . . . .	12
<b>Table 10.</b>	Package dimensions . . . . .	18
<b>Table 11.</b>	Order code . . . . .	22
<b>Table 12.</b>	Document revision history . . . . .	23

## List of figures

<b>Figure 1.</b>	PWD5T60 block diagram . . . . .	2
<b>Figure 2.</b>	PWD5T60 pin connection . . . . .	3
<b>Figure 3.</b>	Switching time definition . . . . .	10
<b>Figure 4.</b>	Normalized gate threshold voltage vs temperature . . . . .	10
<b>Figure 5.</b>	Normalized drain-source breakdown voltage vs. temperature . . . . .	10
<b>Figure 6.</b>	Static drain-source on-resistance . . . . .	11
<b>Figure 7.</b>	Normalized on-resistance vs temperature . . . . .	11
<b>Figure 8.</b>	Transfer characteristics . . . . .	11
<b>Figure 9.</b>	Output characteristics . . . . .	11
<b>Figure 10.</b>	Static source-drain diode forward characteristics. . . . .	11
<b>Figure 11.</b>	VCC power ON and UVLO, LVG timing . . . . .	13
<b>Figure 12.</b>	VCC power ON and UVLO, HVG timing. . . . .	13
<b>Figure 13.</b>	V <sub>BO</sub> power-ON and UVLO timing . . . . .	14
<b>Figure 14.</b>	Smart shutdown timing waveforms . . . . .	16
<b>Figure 15.</b>	Typical application 3-phase single-shunt . . . . .	17
<b>Figure 16.</b>	Package outline . . . . .	20
<b>Figure 17.</b>	Suggested footprint (top view) . . . . .	21

**IMPORTANT NOTICE – READ CAREFULLY**

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgment.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, refer to [www.st.com/trademarks](http://www.st.com/trademarks). All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2024 STMicroelectronics – All rights reserved